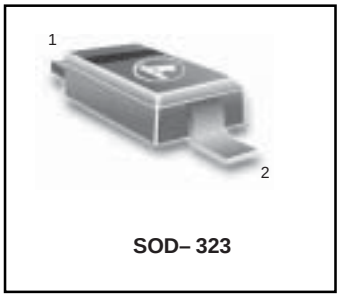
High-speed diode

LBAS316T1G
S-LBAS316T1G



SOD– 323

CATHODE ANODE

DESCRIPTION

The LBAS316T1 is a high-speed switching diode fabricated in planar technology, and encapsulated in the SOD323(SC76) SMD plastic package.

FEATURES

- Ultra small plastic SMD package
- High switching speed: max. 4 ns
- Continuous reverse voltage: max. 75 V
- Repetitive peak reverse voltage: max. 100 V
- Repetitive peak forward current: max. 500 mA.
- We declare that the material of product compliance with RoHS requirements.
- S- Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.

APPLICATIONS

- High-speed switching in e.g. surface mounted circuits.

ORDERING INFORMATION

Device	Marking	Shipping
LBAS316T1G S-LBAS316T1G	Z9	3000 Tape & Reel
LBAS316T3G S-LBAS316T3G	Z9	10000 Tape & Reel

ELECTRICAL CHARACTERISTICS T_j=25°C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MAX.	UNIT
V_F	forward voltage	see Fig.2 I_F = 1 mA	715	mV
		I_F = 10 mA	855	mV
		I_F =50 mA	1	V
		I_F = 150 mA	1.25	V
I_R	reverse current	see Fig.4 V_R = 25 V	30	nA
		V_R =75 V	1	µA
		V_R = 25 V; T_j = 150 °C	30	µA
		V_R = 75 V; T_j = 150 °C;	50	µA
C_d	diode capacitance	f = 1 MHz; V_R = 0; see Fig.5	2	pF
t_{rr}	reverse recovery time	when switched from I_F=10mA to I_R = 10mA; R_L = 100 Ω; measured at I_R = 1 mA; see Fig.6	4	ns
V_{fr}	forward recovery voltage	when switched from IF = 10 mA; tr = 20 ns; see Fig.7	1.75	V

LIMITING VALUES In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{RRM}	repetitive peak reverse voltage		–	100	V
V_R	continuous reverse voltage		–	75	V
$V_{R(RMS)}$	RMS reverse voltage		–	53	V
I_F	continuous forward current		–	250	mA
I_{FRM}	repetitive peak forward current		–	500	mA
I_{FSM}	non-repetitive peak forward current	square wave; T_j=25°C prior to surge; see Fig.3			
		t =1µs	–	5	A
		t =1 ms	–	1	A
		t =1 s	–	0.5	A
P_{tot}	total power dissipation		–	200	mW
$R_{\theta JA}$	thermal resistance junction to ambient air		–	625	°C/W
T_{stg}	storage temperature		-55	+150	°C
T_j	junction temperature		–	150	°C

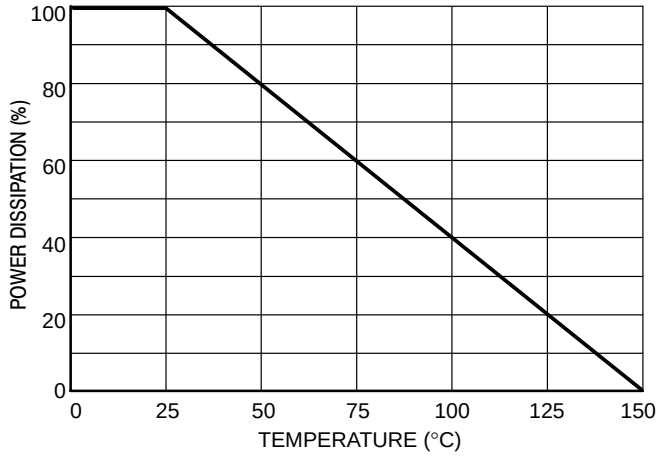


Fig.1 Steady State Power Derating

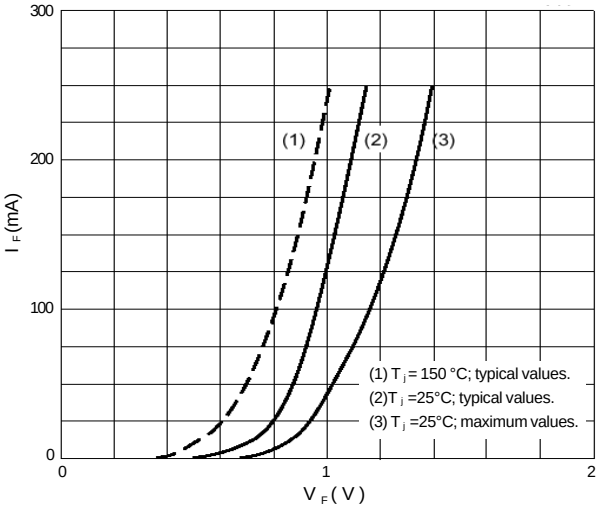


Fig.2 Forward current as a function of forward voltage.

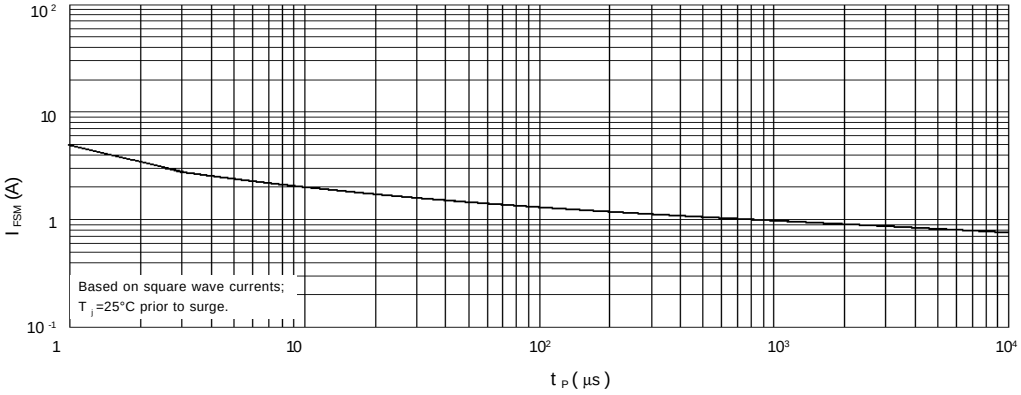


Fig.3 Maximum permissible non-repetitive peak forward current as a function of pulse duration.

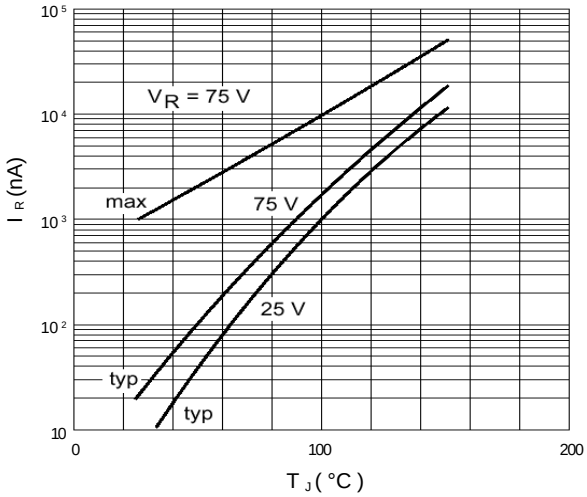


Fig.4 Reverse current as a function of junction temperature.

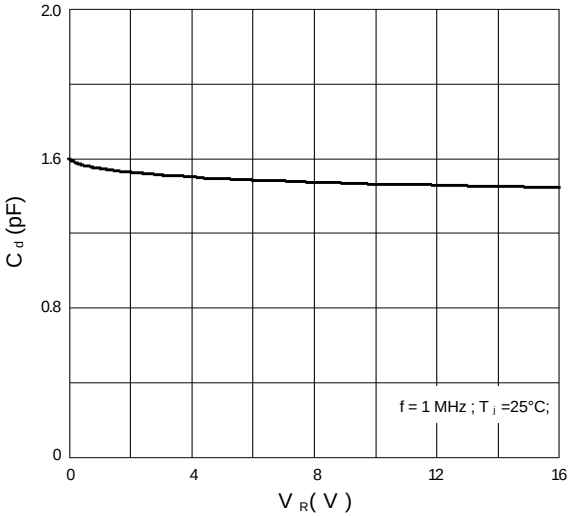
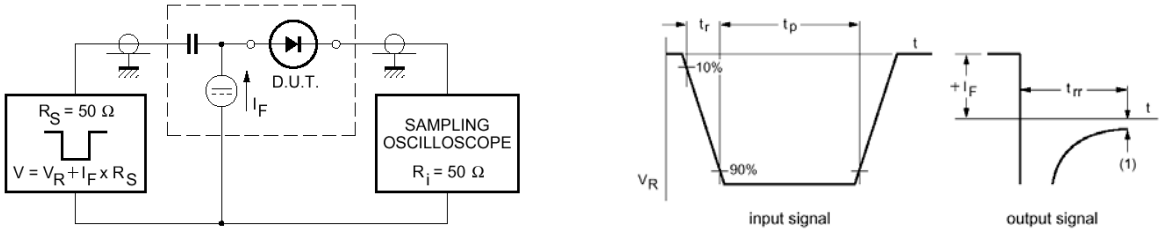


Fig.5 Diode capacitance as a function of reverse voltage; typical values.

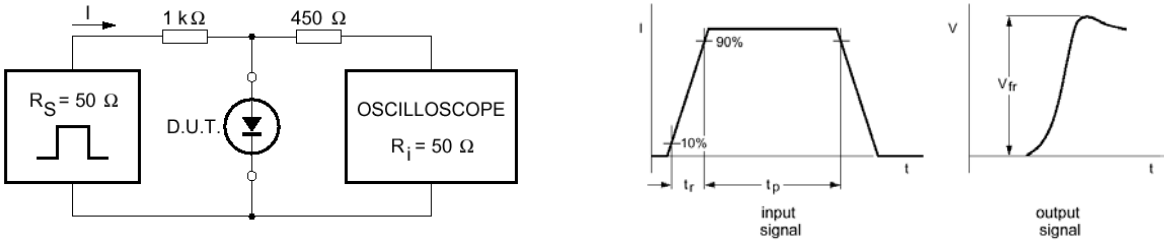


(1) I_R = 1 mA.

Input signal: reverse pulse rise time t_r = 0.6 ns; reverse voltage pulse duration t_p = 100 ns; duty factor δ = 0.05;

Oscilloscope: rise time t_r = 0.35 ns.

Fig.6 Reverse recovery voltage test circuit and waveforms.



Input signal: forward pulse rise time t_r = 20 ns; forward current pulse duration $t_p \geq$ 100 ns; duty factor δ ≤ 0.005.

Fig.7 Forward recovery voltage test circuit and waveforms.

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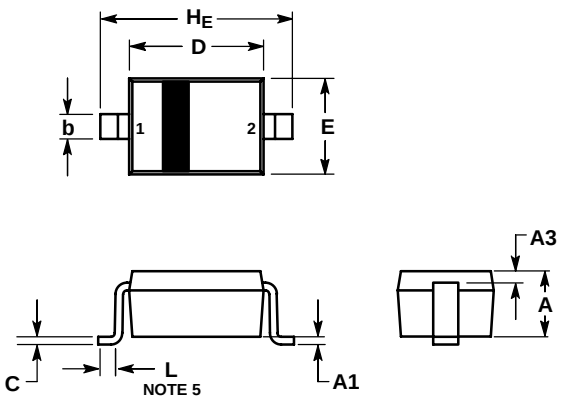
PACKAGE DIMENSIONS
SOD-323



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. LEAD THICKNESS SPECIFIED PER L/F DRAWING WITH SOLDER PLATING.
4. DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.
5. DIMENSION L IS MEASURED FROM END OF RADIUS.

	MILLIMETERS			INCHES		
DIM	**MIN**	**NOM**	**MAX**	**MIN**	**NOM**	**MAX**
A	0.80	0.90	1.00	0.031	0.035	0.040
A1	0.00	0.05	0.10	0.000	0.002	0.004
A3	0.15 REF			0.006 REF		
b	0.25	0.32	0.4	0.010	0.012	0.016
C	0.089	0.12	0.177	0.003	0.005	0.007
D	1.60	1.70	1.80	0.062	0.066	0.070
E	1.15	1.25	1.35	0.045	0.049	0.053
L	0.08			0.003		
H_E	2.30	2.50	2.70	0.090	0.098	0.105

SOLDERING FOOTPRINT*